

~~61.~~ (Amended) A display device comprising:

- a substrate;
- a semiconductor island comprising silicon provided over said substrate;
- a source region and a drain region provided in said semiconductor island;
- a channel region provided in said semiconductor island between said source region and said drain region;
- a gate electrode provided adjacent to said channel region with a gate insulating film therebetween;
- a gate interconnection provided in a same layer as said gate electrode;
- a layer comprising metal provided over said substrate and being in direct contact with said gate interconnection and being connected with one of said source region and said drain region;
- an interlayer dielectric provided over said gate electrode and said layer comprising metal;
- a contact hole provided over said layer comprising metal in said interlayer dielectric; and
- a top layer interconnection comprising aluminum provided over said interlayer dielectric and connected with said layer comprising metal through said contact hole.

~~73.~~ (Amended) A semiconductor device comprising:

a substrate;

a semiconductor island comprising silicon provided over said substrate;

a source region and a drain region provided in said semiconductor island;

a channel region provided in said semiconductor island between said source region and said drain region;

a gate electrode provided adjacent to said channel region with a gate insulating film therebetween;

~~DA~~ a gate interconnection provided in a same layer as said gate electrode;

a layer comprising metal provided over said substrate and being in direct contact with said gate interconnection and being connected with one of said source region and said drain region, said layer comprising metal being connected with said gate interconnection through no contact hole;

an interlayer dielectric provided over said gate electrode and said layer comprising metal;

a contact hole provided over said layer comprising metal in said interlayer dielectric; and

a top layer interconnection comprising aluminum provided over said interlayer dielectric and connected with said layer comprising metal through said contact hole.

74. (Amended) A semiconductor device comprising:

- a substrate;
- a semiconductor island comprising silicon provided over said substrate;
- a source region and a drain region provided in said semiconductor island;
- a channel region provided in said semiconductor island between said source region and said drain region;
- ~~72~~ a gate electrode provided adjacent to said channel region with a gate insulating film therebetween;
- a gate interconnection provided in a same layer as said gate electrode;
- a layer comprising metal provided over said substrate and being in direct contact with said gate interconnection and being connected with one of said source region and said drain region;
- an interlayer dielectric comprising silicon nitride provided over said gate electrode and said layer comprising metal;
- a contact hole provided over said layer comprising metal in said interlayer dielectric; and
- a top layer interconnection comprising aluminum provided over said interlayer dielectric and connected with said layer comprising metal through said contact hole.

75. (Amended) A semiconductor device comprising:

- a substrate;
- a semiconductor island comprising silicon provided over said substrate;
- a source region and a drain region provided in said semiconductor island;
- a channel region provided in said semiconductor island between said source region and said drain region;
- ~~12~~ a gate electrode provided adjacent to said channel region with a gate insulating film therebetween;
- a gate interconnection provided in a same layer as said gate electrode;
- a layer comprising metal provided over said substrate and being in direct contact with said gate interconnection and being connected with one of said source region and said drain region;
- an interlayer dielectric comprising silicon oxide provided over said gate electrode and said layer comprising metal;
- a contact hole provided over said layer comprising metal in said interlayer dielectric; and
- a top layer interconnection comprising aluminum provided over said interlayer dielectric and connected with said layer comprising metal through said contact hole.

76. (Amended) A semiconductor device comprising:

a substrate;

a semiconductor island comprising silicon provided over said substrate;

a source region and a drain region provided in said semiconductor island;

a channel region provided in said semiconductor island between said source region and said drain region;

12 a gate electrode comprising a doped polycrystalline silicon provided adjacent to said channel region with a gate insulating film therebetween;

a gate interconnection provided in a same layer as said gate electrode;

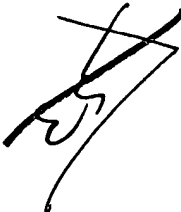
a layer comprising metal provided over said substrate and being in direct contact with said gate interconnection and being connected with one of said source region and said drain region;

an interlayer dielectric provided over said gate electrode and said layer comprising metal;


a contact hole provided over said layer comprising metal in said interlayer dielectric; and

a top layer interconnection comprising aluminum provided over said interlayer dielectric and connected with said layer comprising metal through said contact hole.

Please add the following new claims.

 86. (New) A display device comprising:

- a substrate;
- a semiconductor island comprising silicon provided over said substrate;
- a source region and a drain region provided in said semiconductor island, said source region and said drain region comprising a silicide of a metal;
- a channel region provided in said semiconductor island between said source region and said drain region;
- a gate electrode provided adjacent to said channel region with a gate insulating film therebetween;
- a gate interconnection provided in a same layer as said gate electrode;
- a layer comprising said metal provided over said substrate and being in direct contact with said gate interconnection and being connected with one of said source region and said drain region;
- an interlayer dielectric provided over said gate electrode and said layer comprising said metal;
- a contact hole provided over said layer comprising said metal in said interlayer dielectric; and



a top layer interconnection comprising aluminum provided over said interlayer dielectric and connected with said layer comprising said metal through said contact hole.

87. (New) A semiconductor device comprising:

a substrate;

a semiconductor island comprising silicon provided over said substrate;

~~73~~ a source region and a drain region provided in said semiconductor island, said source region and said drain region comprising a silicide of a metal;

a channel region provided in said semiconductor island between said source region and said drain region;

a gate electrode provided adjacent to said channel region with a gate insulating film therebetween;

a gate interconnection provided in a same layer as said gate electrode;

a layer comprising said metal provided over said substrate and being in direct contact with said gate interconnection and being connected with one of said source region and said drain region, said layer comprising said metal being connected with said gate interconnection through no contact hole;

an interlayer dielectric provided over said gate electrode and said layer comprising said metal;

a contact hole provided over said layer comprising said metal in said interlayer dielectric; and

~~DS~~ a top layer interconnection comprising aluminum provided over said interlayer dielectric and connected with said layer comprising said metal through said contact hole.

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